

# **isc** Silicon NPN Power Transistor

# 2SC5199

### DESCRIPTION

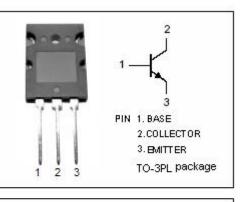
- High Current Capability
- High Power Dissipation
- · High Collector-Emitter Breakdown Voltage-
- : V<sub>(BR)CEO</sub>= 160V(Min)
- Complement to Type 2SA1942
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

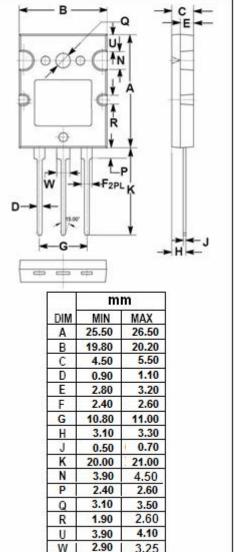
## **APPLICATIONS**

- Power amplifier applications
- Recommend for 80W high fidelity audio frequency amplifier output stage applications

### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	160	V
V <sub>CEO</sub>	Collector-Emitter Voltage	160	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
lc	Collector Current-Continuous	12	A
I <sub>B</sub>	Base Current-Continuous	1.2	A
Pc	Collector Power Dissipation @ Tc=25°C	120	W
TJ	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C





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3.25



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## **ELECTRICAL CHARACTERISTICS**

### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	160			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 8.0A; I <sub>B</sub> = 0.8A			2.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 6A; V <sub>CE</sub> = 5V			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 160V; I <sub>E</sub> = 0			5	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			5	μA
hfe-1	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	55		160	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 6A; V <sub>CE</sub> = 5V	35			
Сов	Output Capacitance	I <sub>E</sub> =0; V <sub>CB</sub> = 10V; f <sub>test</sub> = 1.0MHz		170		pF
fT	Current-Gain—Bandwidth Product	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V		30		MHz

### • h<sub>FE-1</sub> Classifications

R	0	
55-110	80-160	



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